

# Effect of Pressure on the Structural and Electronic Properties of ZnS

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## Abstract

We study the electronic and structural properties of zinc-sulphide (ZnS) under high pressure, using large unit cell method. We employ intermediate neglect of differential overlap calculations, with appropriate corrections to the band gap and zero point energy to the cohesive energy. The results are in reasonable agreement with available experimental data. The applied pressure on zinc-sulphide causes the following effect; an increase of the band gap, the valence bandwidth and the cohesive energy, and a decrease of the conduction bandwidth. This model predicts a decrease of the electronic occupation probability for the s and p orbital of sulfur with an increase of this probability for the s-orbital of zinc with the increase of pressure.

## تأثير الضغط في الخصائص التركيبية والالكترونية لكبريتيد الزنك

### الخلاصة

تم في هذا البحث دراسة الخواص الالكترونية والتركيبية لكبريتيد الزنك (ZnS) تحت تأثير الضغوط العالية باستعمال طريقة خلية الوحدة الكبيرة. حيث تم استعمال حسابات الإهمال المتوسط للتداخل التفاضلي مع إجراء تصحيحات مناسبة لفجوة الطاقة وطاقة نقطة الصفر إلى طاقة الترابط. النتائج التي تم الحصول عليها كانت متطابقة إلى حد مقبول مع النتائج العملية المتوفرة. إن الضغط المسلط على البلورة قيد الدراسة أدى إلى التأثيرات التالية: زيادة كل من فجوة الطاقة وعرض حزمة التكافؤ وطاقة الترابط، ونقصان عرض حزمة التوصيل. إن هذا النموذج يتوقع نقصان احتمالية وجود الالكترونات في المدارين s و p للكبريت مع زيادة هذه الاحتمالية للمدار s في الزنك بزيادة الضغط المسلط.

## 1. Introduction

Calculation of the bulk ground state properties, such as lattice constants, bond lengths, bulk modulus, cohesive energy, and atomic positions, play an important role in the physics of condensed matter [Schröder, 2000; Persson and Jenzen, 1998; Wachowicz and Kiejna, 2001]. Bulk calculations help us to understand, characterize, and predict mechanical properties of materials in surroundings, under extreme conditions, as in geological formations and settings, and for industrial applications. Crystalline materials come in many different structures and in contrast to isotropic materials; the description of the ground state of crystalline may in general need multiple lattice parameters and an atomic basis.

In recent years, several theoretical and experimental studies have focused on the electronic properties of ZnS semiconductor largely motivated by the potential applications of these materials in opto-electronic devices, particularly blue-green lasers [Wherrett, 1996] and in technological applications mainly in the field of optical devices.

In this work we have studied the effect of pressure on the some properties of zinc - sulphide (ZnS) in the zinc-blende phase using the self-consistent large unit cell within intermediate neglect of differential overlap (LUC-INDO) method depends on the linear combination of atomic orbitals approximation [Harker and Larkins, 1979; Radi *et al.*, 2007]. This method, which had been already successfully employed for a long time in molecular theory has gained wide acceptance in calculations of the electronic structures of crystals.

## 2. Structural Properties and Phase Transition of ZnS

Zinc sulphide crystallizes under normal conditions with the zinc-blende (ZB) structure [López-Solano, 2003; Mujica, 2003], in the four fold coordinated which corresponds to the space group ( $\Gamma\bar{A}3m$ ). As the pressure is applied to ZnS it transforms into rock-salt phase (NaCl) with six-fold coordinated, Smith and Martin [Smith and Martin, 1965] reported a transition pressure of 11.7 GPa, although later studies have placed it at a somewhat higher pressure 14.5 GPa according to Nelmes and McMahon [Nelmes and McMahon, 1998] and 15.5 GPa according to Uchino et al [Uchino *et al.*, 1999]. In contrast to zinc-blende structure, the NaCl phase is found to an indirect-gap semiconductor [Ves *et al.*, 1990; Zhou, 1991], which has been confirmed by a first - principles calculations [Jaffe *et al.*, 1993]. At the pressure about 65 GPa the NaCl phase has been reported to undergo a Cmc $m$ -like distortion with no significant change in volume [Desgreniers *et al.*, 2000; Nelmes and McMahon, 1998]. The high pressure behavior of ZnS has been the subject of several recent theoretical [Mujica *et al.*, 2003; Qteish and Muñoz, 2001] and experimental [Desgreniers *et al.*, 2000] studies.

## 3. Computational Details

The basic idea of the large unit cell is in computing the electronic structure of the unit cell extended in a special manner at  $k=0$  in the reduced Brillouin zone. This is equivalent to a band structure calculation at those  $k$ -point; which transform to Brillouin zone center on extending the unit cell [Graig and Smith, 1987]. Using the linear combination of atomic orbitals LCAO, the crystal wavefunction in the LUC-INDO formalism is written in the following form [Radi *et al.*, 2007]:

$$\psi_a(k, r) = \sum_u \sum_p^{cellsbasis} \exp(ikR_u) C_{pa}(k) \phi_p(r - R_u) \quad (1)$$

where  $C_{pa}$  are the orbital expansion coefficients, the  $R_u$  is the lattice translation vector,  $r$  is a position vector and  $k$  is the wave vector. The atomic orbitals used for the LCAO procedure form the basis set of the calculation. We expand the wavefunction in a set of Slater-type orbitals (STO), this is very efficient basis set, and these orbitals have the radial form [Slater, 1974]:

$$R_{nl}(r) = \frac{(2\zeta)^{n+1/2}}{(2n!)^{1/2}} r^{n-1} \exp(-\zeta r) \quad (2)$$

where  $\zeta$  the orbital exponent. The expectation value of the electronic energy is:

$$\varepsilon = \langle \Psi | H | \Psi \rangle / \langle \Psi | \Psi \rangle \quad (3)$$

The Hamiltonian for a microcrystal consisting of N electrons may be written as [Chelikowsky and Saad, 2004]

$$H = \sum_a^N \left( -\frac{1}{2} \nabla_a^2 - \sum_A^{n_A} Z_A r_{AA}^{-1} \right) - \frac{1}{2} \sum_a^N \sum_p^N r_{ap}^{-1} + \sum_A^{n_A} \sum_B^{n_B} Z_A Z_B R_{AB}^{-1} \quad (4)$$

where  $Z_A$  is the core charge,  $R_{AB}$  is the distance between the atoms A and B, and the summation is over all nuclei. But the Roothaan-Hall equations can be obtained [Everstov and Lovchikov, 1977]:

$$\sum_p (F_{pqk} - \varepsilon_a S_{pqk}) C_{pqk} = 0 \quad (5)$$

$F_{pqk}$  represents the Fock matrix elements and  $S_{pq}$  is the overlap integral for atomic function  $\phi_q$  and  $\phi_p$ , and can be written in the form [Radi *et al.*, 2007]:

$$S_{pqk} = \sum_u \langle \phi_p(r - R_0) | \phi_q(r - R_u) \rangle \exp(ikR_u) \quad (6)$$

The Fock matrix elements may be represent as the sum of the one- and two- electron interactions:

$$F_{op,uq} = \left\langle \phi_p^1(1) \left| -\frac{1}{2} \nabla_1^2 - \sum_a Z_a r_{1a}^{-1} \right| \phi_q^u(1) \right\rangle + \sum_{v,\lambda}^{cellbasis} \sum_{rs} P_{rs}^{v\lambda} \left( (\phi_p^o \phi_q^u | \phi_r^v \phi_s^\lambda) - \frac{1}{2} (\phi_p^o \phi_r^v | \phi_s^\lambda \phi_q^u) \right) \quad (7)$$

$P_{rs}^{v\lambda}$  is the density element with the form:

$$P_{rs}^{v\lambda} = 2 \sum_{k'} \sum_a^{occ} C_{rak'}^* C_{sak'} \exp ik' \cdot (R_\lambda - R_\nu) \quad (8)$$

In equation (5) if  $k=0$  then

$$\sum_p (F_{pq0} - \varepsilon_a S_{pq0}) C_{pq0} = 0 \quad (9)$$

In INDO approximation one can utilize that many of the integrals are very small or zero and begin to neglect systematically some of the matrix elements and many approximations can be made. The Fock matrix elements in their final forms in the LUC-INDO formalism used in this work [Harker and Larkins, 1979] are as follow:

$$F_{pp(0)} = U_{op,op} - \sum_{A \neq B} \sum_v Z_B \gamma_{AB}^{ov} + \sum_v \beta_A^0 (S_{op,vp} - \delta_{ov}) + \sum_r \sum_v P_{rr}(0) \gamma_{AB}^{ov} - \frac{1}{2} \sum_{v \neq 0} P_{pp}(0) f(x) \gamma_{AA}^{ov} - \frac{1}{2} \sum_r P_{rr}(0) (\phi_p^r \phi_r^o | \phi_p^o \phi_r^o) \quad (10)$$

$$F_{pq(0)} = \sum_v \beta_{AB}^0 S_{op,vp} - \frac{1}{2} \sum_v P_{pq}(0) f(x) \gamma_{AB}^{ov} \quad (11)$$

For p and q on different atomic centers, and

$$F_{pq(0)} = \sum_v \beta_A^0 S_{op,vp} - \frac{1}{2} \sum_{v \neq 0} P_{pq}(0) f(x) \gamma_{AA}^{ov} + \frac{1}{2} P_{pq}(0) [(\phi_p^o \phi_q^o | \phi_r^o \phi_s^o) - (\phi_p^o \phi_r^o | \phi_s^o \phi_q^o)] \quad (12)$$

For p and q on the same atomic center,  $\beta_{AB}$  is the bonding parameter and  $\gamma_{AB}$  is the average electrostatic repulsion between any electron on atom A and any electron on atom B, where  $U_{pp}$  is the local core matrix element can be written as [Pople and Beveridge, 1970]:

$$U_{pp} = -\frac{1}{2}(I_p + A_p) + (Z_A - \frac{1}{2})\gamma_{AA} \quad (13)$$

where  $I_p$  and  $A_p$  are the ionization potential and electron affinity, respectively,  $f(x)$  in equation (12) is the modulating function and is given by [Szymanski, 1984]

$$f(x) = \left(\frac{\sin x}{x}\right)^2 \quad (14)$$

For the eight atoms LUC,  $x$  is given by

$$x = \frac{\pi R_{AB}}{a} \quad (15)$$

$R_{AB}$  is the distance between the atom A at the central lattice o and the atom B at the v lattice.

## 4. Results and Discussion

### 4.1 Choice of Parameters

The empirical parameters in the LUC–INDO method are the orbital exponent  $\zeta$ , the bonding parameter  $\beta$ , the electronegativity of s-orbital ( $E_s$ ), and the electronegativity of p-orbital ( $E_p$ ). The value of the orbital exponent determines the charge distribution of electrons around the nucleus or in the solid. These parameters are varied firstly to give nearly the exact value of the equilibrium lattice constant, cohesive energy, indirect band gap and valence band widths. The optimum values of these parameters used for ZnS in the present work are listed in Table 1.

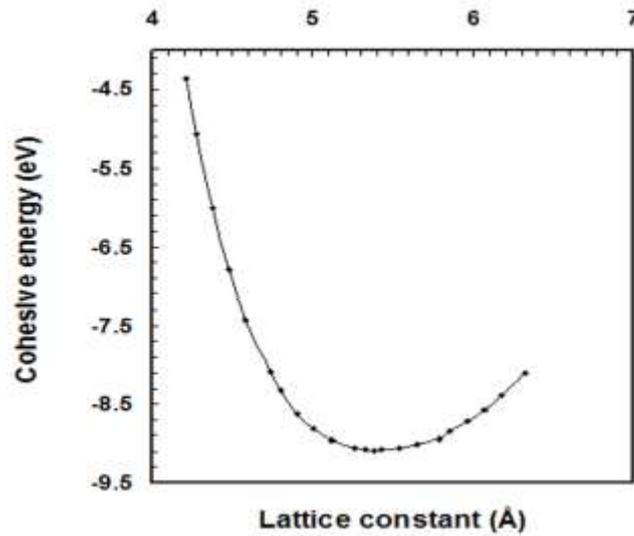
**Table 1.** Parameters set of ZnS used in this work.

Parameter	Zn	S
$\zeta$ ( a.u) <sup>-1</sup>	2.0038	2.112
$\beta_{AB}$ (eV)	-17.17	-20.23
$E_s$ (eV)	15.57	19.43
$E_p$ (eV)	6.97	8.26

The results of cohesive energies as a function of lattice constant are obtained by the above method at 0 K and zero pressure. The equilibrium lattice constant obtained from LUC-INDO calculations for ZnS is listed in Table 2 in comparison with experimental and theoretical results. The lattice constant for ZnS presents here is

slightly smaller than experimental calculations, the difference between the experimental data and our results are very small, i.e., is about only 0.03 Å.

Figure 1 is fitted to the Murnaghan's equation of state [Ziambaras and Schröder, 2003], from which we obtain the equilibrium lattice parameter  $a_0$ , the bulk modulus  $B$ , and its derivative  $B'_0$ .



**Figure 1.** Cohesive energy as a function of lattice constant for ZnS.

Based on these calculations, we obtained that the cohesive energy value of the present work is in good agreement with the experimental result (as shown in Table 2). We added the free atom  $sp$  shell energy ( $E_{free}$ ), for the cohesive energy to correct its value. In this work  $E_{free} = 151.86$  eV, and this value is taken from the ionization potential of ZnS. On the other hand, the zero-point vibration energy ( $E_0$ ) is neglected because its very small = 0.085 eV. The calculated direct bandgap is listed in Table 2 and the difference between LUC-INDO and experimental result of direct bandgap is relatively small, where the computed band gap value is higher than experimental value, this is mainly due to a consequence of two approximations made in this calculation. First, the core structure was ignored, through some compensation results from using semiempirical parameters. Second, using minimal basis set atomic orbitals (without considering any excited levels). The calculated bulk modulus of ZnS is 74 GPa, which is in good agreement with the experimental values of 76.9 GPa [Modelung, 1982] and 79.5 GPa [Abrikosov *et al.*, 1969]. Hybridization states show an increasing  $s$ -state occupation with the decreasing atomic number of the compound where the occupation of  $s$  state of sulfur is larger than of that for zinc. The eigenvalues of the high symmetry points are shown in Table 3.

**Table 2.** Electronic and structural properties calculated within the large unit cell at ground state (zero pressure and 0 K temperature).

Property	Present	Experimental	Theoretical
Lattice constant (Å)	5.381	5.411 [Abrikosov <i>et al.</i> , 1969]	5.30 [Chen <i>et al.</i> 1996]; 5.35 [Yeh <i>et al.</i> , 1992]
Cohesive energy (eV)	9.08	8.97 [Weidemann <i>et al.</i> , 1992]	7.4 [Lou <i>et al.</i> , 2002]; 8.33 [Oshikiri <i>et al.</i> , 1999]
Conduction bandwidth (eV)	1.89	.....	.....
Valence bandwidth (eV)	12.45	.....	.....
Band gap (eV)	4.242	3.82 [Strehlow and Cook, 1973]	3.24 [Kotani <i>et al.</i> , 2002]; 3.98 [Zakharov <i>et al.</i> , 1994]
Hybridization state of S	$s^{1.86} p^{4.53}$	$s^2 p^4$	.....
Hybridization state of Zn	$s^{1.65}$	$s^2$	.....

**Table 3.** Eigenvalue of ZnS at high symmetry points, compared with other result.

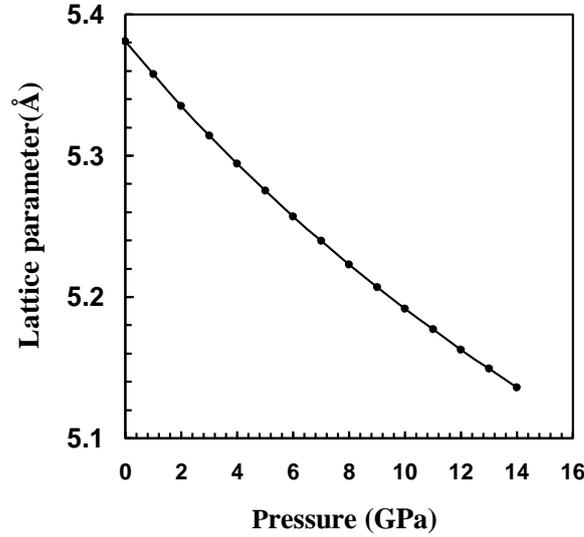
Symmetry point	Eigenvalue (eV)	
	Present	Reference [ Chen <i>et al.</i> 1996]
$\Gamma_{1v}$	-12.45	-13.51
$\Gamma_{15v}$	0	0
$\Gamma_{1c}$	4.242	2.15
$\Gamma_{15c}$	7.32	6.49
$X_{1v}$	- 11.12	- 12.05
$X_{5v}$	- 4.51	- 4.87
$X_{1c}$	4.34	3.18
$X_{4c}$	6.23	4.02

## 4.2 Effect of Pressure on the Properties

The effect of pressure on the electronic structure and other properties can be calculated from the present theory and computational procedure. By the use of our calculated values of the bulk modulus  $B$ , and its derivative  $B'_0$ , the volume change ( $V_0$ ) with applied pressure was calculated using the following equation [Wang and Ye, 2005]

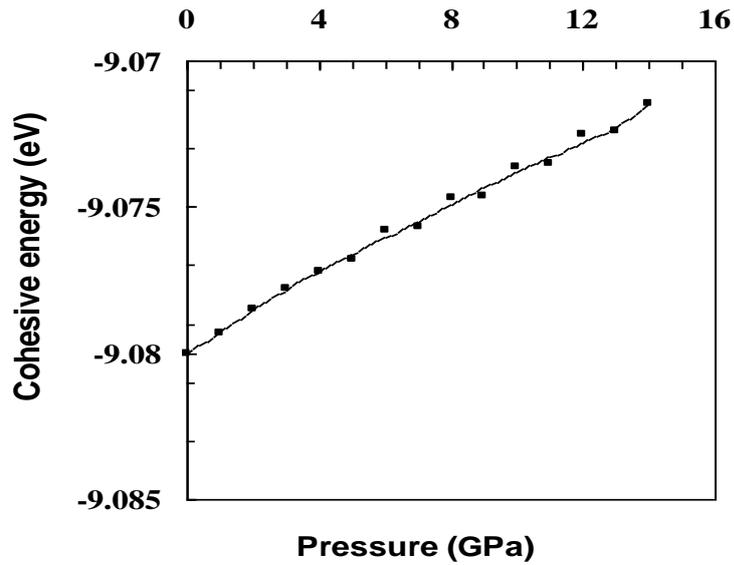
$$P = \frac{B_0}{B'_0} \left[ \left( \frac{V_0}{V} \right)^{B'_0} - 1 \right] \quad (16)$$

where  $P$  is pressure and  $V_0$  is the equilibrium volume at zero pressure. We applied a pressure up to 14 GPa, because this structure transforms to another phase, rock salt (NaCl), when pressure exceeds nearly 14 GPa [Nelmes and McMahon, 1998]. The calculated lattice constant as a function of pressure is shown in Fig.2.



**Figure 2.** Lattice constant as a function of pressure using LUC –INDO model.

The pressure dependence of the cohesive energy is illustrated in Fig.3. It is shown that the absolute value of the cohesive energy decreases as the pressure increases. The pressure derivative of the high symmetry points ( $\Gamma_{1v}$ ,  $\Gamma_{15v}$ ,  $X_{1v}$ ,  $X_{5v}$ ,  $X_{1c}$ ,  $X_{5c}$ ,  $\Gamma_{15c}$ , and  $\Gamma_{1c}$ ) is shown in table 4. From this table one can see that the eigenvalues at the conduction band ( $X_{5c}$ ,  $\Gamma_{15c}$ ,  $\Gamma_{1c}$ ,  $X_{1c}$ ) increase with pressure, whereas eigenvalues at the valence band ( $X_{5v}$ ,  $X_{1v}$ ,  $\Gamma_{1v}$ ) decrease with pressure. However, the decrease of  $X_{5v}$ ,  $X_{1v}$ , and  $\Gamma_{1v}$  with pressure is small.

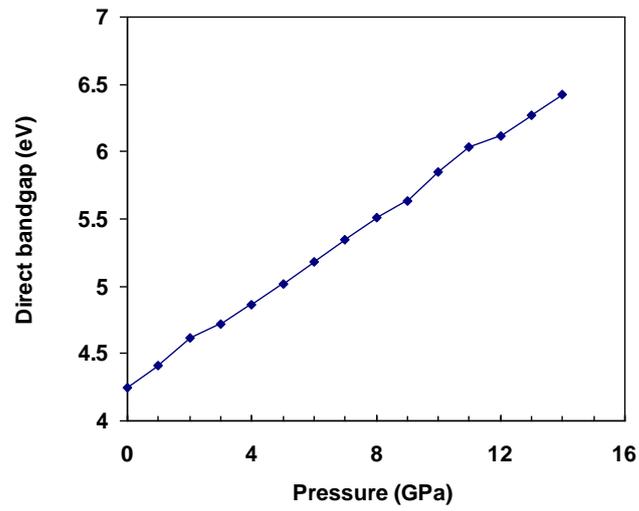


**Figure 3.** Cohesive energy versus pressure for ZnS.

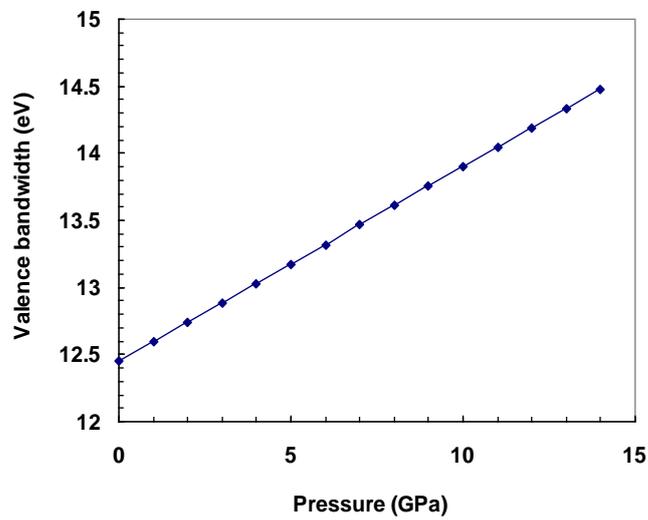
**Table 4 .**The pressure derivative of the high symmetry points, where the minus sign means that the high symmetry point decreases with pressure effect.

Symmetry point	The pressure derivative (meV/GPa )
$\Gamma_{1v}$	-18.6
$\Gamma_{1c}$	51.22
$\Gamma_{15c}$	27.7
$X_{1v}$	-21.3
$X_{5v}$	-15.2
$X_{1c}$	43.04
$X_{4c}$	31.2

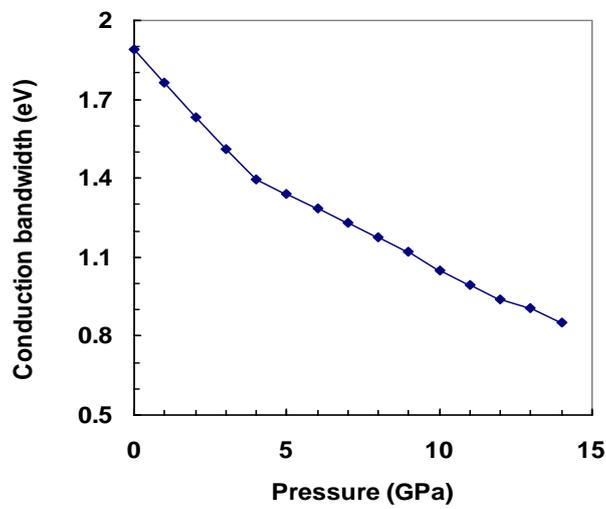
The pressure derivative of the direct bandgap is shown in figure 4. From this figure we can see that the direct band gap increases with the increase of pressure. The predicted effect of pressure on the valence bandwidth and conduction bandwidth is illustrated in Figures 5 and 6, respectively. The valence bandwidth increases with the increase of pressure, while the conduction bandwidth decreases with the increase of pressure.



**Figure 4.** The effect of pressure on the bandgap of ZnS.

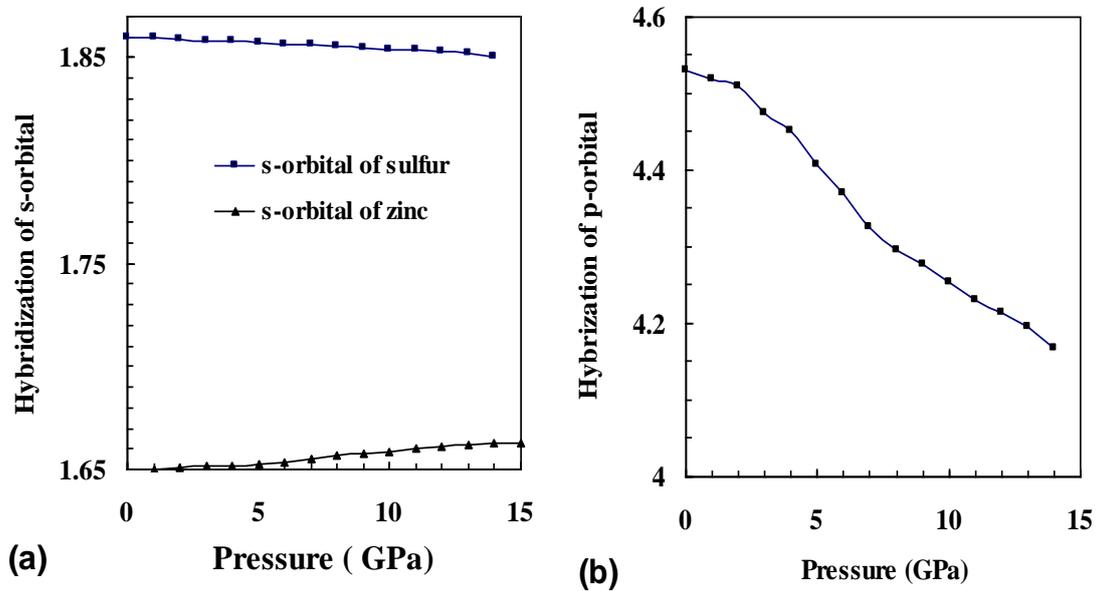


**Figure 5.** Pressure dependence of the valence bandwidth of ZnS.



**Figure 6.** Predicted effect of pressure on the conduction bandwidth of ZnS.

We found that the s and p states occupation of S decreases with the increase of pressure, whereas the s states occupation of Zn increases in this case. The occupation of s and p states for S and Zn with pressure is shown in Fig.7. The increase of pressure causes an increase of the probability of electron transition from sulfur to zinc. This is known and leads to a phase transition due to the change of electronic distribution such as the s-d transition in alkali metals [Takemura and Syassen, 1983].



**Figure 7.** The effect of pressure on the hybridization of (a) s- state and (b) p- state.

## Conclusions

In conclusion, we applied large unit cell within the intermediate neglect of differential overlap method to study the structure and electronic properties of ZnS semiconductor under the effect of pressure. The calculated results indicate that this model gives results in good agreement with the corresponding experimental results, and this shows the possibility of using this model in qualitative of study some materials. The properties obtained are in good agreement with the existing experimental data and with GDSF/DFT except the direct band gap which is greater than the experimental data, this difference is due to the neglect to the core states and to the approximations incorporated with the computational formalism. A reasonable agreement for the valence bandwidth and band gaps is shown in comparison with available theoretical results even when these values are not in a good agreement with the corresponding experimental values. The effect of pressure on these properties is investigated. It is found that the conduction bandwidth decreases with increasing the pressure, whereas the direct and indirect bandgap, valence bandwidth, and cohesive energy increase with the increase of pressure. The maximum value of pressure is taken to be 14 GPa, because beyond this value of pressure, the phase of ZnS transforms from ZB to rock salt phase. Relativistic effect is added to the calculation of the band gap, also zero point energy is added to the calculation of the cohesive energy. Finally, this model is shown to give good description to the hybridization state and charge density of ZnS and it is expected that this method could give reliable description for other materials that has zinc-blende and cubic structure.

## References

- Abrikosov, N. K., Bankina, V. B., Poretskaya, L. V., Shelimova, L. E., and Skudnova, E. V., 1969, "*Semiconducting II-VI, IV-VI, and V-VI Compounds*", (Plenum, New York), p. 2.
- Chelikowsky, J., and Saad, Y., 2004, "*Electronic structure of clusters and Nanocrystals*", University of Minnesota.
- Chen, X., Hua, X., Hu, J., Langlois, J., and Goddard III, W. A., 1996, "Band structure of II- VI semiconductors using Gaussian basis functions with separable ab initio pseudopotentials: Application to prediction of band offsets", *Phys. Rev. B* 53, pp 1377- 1387.
- Craig, B. J., and Smith, P. V., 1987, "Beyond the LUC-CNDO  $k = 0$  approximation", *phys. stat. sol. (b)* 140, pp 491-500.
- Desgreniers, S., Beaulieu L., and Lepage, I., 2000, "Pressure-induced structural changes in ZnS", *Phys. Rev. B* 61, pp 8726 -8733.
- Evarestov, R., and Lovchikov, V., 1977, "Large unit cell calculations of solids in the CNDO approximation", *phys. stat. sol. (b)*, 79, pp 743-751.
- Harker, A. H., and Larkins, F. P., 1979, "A large unit cell semiempirical molecular orbital approach to the properties of solids. I. General theory", *J. Phy.C: Solid State Phys.* 12, pp 2487-2495.
- Jaffe, J. E., Pandey, R., and Seel, M. J., 1993, "Ab initio high-pressure structural and electronic properties of ZnS", *Phys. Rev. B* 47, pp 6299- 6303.
- Kotani, T., and van Shilfgaarde, M., 2002, "All-electron GW approximation with the mixed basis expansion based on the full-potential LMTO method", *Solid State Commun.* 121, pp 461- 465.
- López-Solano, J., Mujica, A. , Rodríguez-Hernández, P., and Muñoz, A., 2003, "Theoretical study of ZnS under high pressure", *Phys. Status Solidi B* 235, p452-455.
- Lou, W., Ismail-Beigi, S., Cohen, M. L. and Louie, S. G., 2002, Quasiparticle band structure of ZnS and ZnSe", *Phys. Rev. B* 66, pp 195215- 19221.
- Mujica, A., Rubio, A., Muñoz, A., and Needs, R. J., 2003, "High – pressure phases of group – IV, III-V, and II-VI compounds", *Rev. Mod. Phys.* 75, pp 863-914.
- Nelmes, R. J., and McMahan, M. I., 1998, *Semicond. Semimetals* 54, pp145.
- Madelung, O., (ed.), Landolt-Börnstein, *Semiconductor, Physics of II-IV anI-VII Compounds, Semimagnetic Semiconductors*, New Series, Group III, V. 17, (Springer, Berlin, 1982).
- Oshikiri, M., and Aryasetiawan, F., 1999, "Band gaps and quasiparticle energy calculations on ZnO, ZnS, and ZnSe in the zinc-blende structure by the GW approximation", *Phys. Rev. B* 60, pp 10754 - 10757.
- Persson, C., and Jenzen, E., 1998, "Electronic band structure in hexagonal close-packed Si polytypes", *J. Phys. Condens. Matter* 10, pp 10549- 10555.
- Pople, J., and Beveridge, D., 1970, "Approximate Molecular Orbital Theory", McGraw – Hill.
- Qteish, A., and Muñoz, A., 2001, "Stability and Structural Properties of ZnS and ZnSe under High Pressure", *phys. stat. sol. (b)* 223, pp 417- 422.
- Radi, I. O., Abdulsattar, M. A., and Abdul-Lettif, A. M., 2007, "Semiempirical LUC-INDO calculations on the effect of pressure on the electronic structure of diamond", *phys. stat. sol. (b)* 244, pp 1304 -1317.
- Schröder, E., 2000, "Nematic liquid-crystal director configuration for general elastic coefficients", *Phys. Rev. E* 62, pp 8830- 8833.
- Slater, J., 1974, "*Quantum Theory of Atomic Structure*", McGraw – Hill.

- Smith, P. L., and Martin, J. E. , 1965," The high-pressure structures of zinc sulphide and zinc selenide", *Phys. Lett.* **19**, pp 541-543.
- Strehlow, W. H., and Cook, E. L., 1973," Compilation of Energy Band Gaps in Elemental and Binary Compound Semiconductors and Insulators", *J. Phys. Chem. Ref. Data* **2**, pp 163-200.
- Szymanski, J. E., 1984,"Semiempirical Methods of Total Energy Calculations", Ph. D., University of York.
- Takemura, K., and Syassen, K.,1983,"High-pressure phase transitions in potassium and phase relations among heavy alkali metals", *Phys. Rev. B* **28**, pp 1193-1196.
- Uchino, M., Mashimo, T., Kodama, M., Kobayashi, T., Takasawa, E., Sekine, T. Noguchi, Y., Hikosaka, H., Fukuoka, K., Syono, Y., Kondo, T., and Yagi, T., 1999," Phase transition and EOS of zinc sulfide under shock and static compressions up to 135 GPa", *J. Phys. Chem. Solids* **60**, pp 827- 837.
- Ves, S., Schwarz, U., Christensen, N. E., Syassen, K., and Cardona, M., 1990," Cubic ZnS under pressure: Optical-absorption edge, phase transition, and calculated equation of state", *Phys. Rev. B* **42**, pp 9113 -9118.
- Wachowicz, E., and Kiejna, A., 2001," Bulk and surface properties of hexagonal-close-packed Be and Mg", *J. Phys.: Condens. Matter* **13**, pp 10767- 10776.
- Wang, S. Q, Ye, H. Q., 2005," Ab initio investigation of the pressure dependences of phonon and dielectric properties for III–V semiconductors", *J. Phys.: Condens. Matter*, **17**, pp 4475- 4488.
- Weidemann, R., Gumlich, H., Kupsch, M., Middelmann, H.-U, and Becker, U., 1992," Partial density of Mn 3d states and exchange-splitting changes in  $Zn_{1-x}Mn_xY$  (Y=S,Se,Te)", *Phys. Rev. B* **45**, pp 1172- 1180.
- Wherrett, B. S., 1996," The nonlinear behaviour of II& unknown;VI materials", *J. Cryst. Growth* **159**, pp766-770.
- Yeh, C., Lu, W., Froyen, S., and Zunger, A., 1992,"Zinc-blende–wurtzite polytypism in semiconductors", *Phys. Rev. B* **46**, pp 10086 -10097.
- Zakharov, O., Rubio, A., Blase, X. Cohen, M. L., and Louie, S. G., 1994,"Quasiparticle band structures of six II-VI compounds: ZnS, ZnSe, ZnTe, CdS, CdSe, and CdTe", *Phys. Rev. B* **50**, pp 10780- 10787.
- Zhou, Y. H., Campbell, A. J., and Heinz, D. L., 1991,"Equations of state and optical properties of the high pressure phase of zinc sulfide", *J. Phys. Chem. Solids* **52**, pp 821- 825.
- Ziambaras, E., Schröder, E., 2003," Theory for structure and bulk modulus determination", *Phys. Rev. B* **68**, pp 064112-1 - 064112-7.